

Publication

EP 0905836 A3 19990414

Application

EP 98115466 A 19980817

Priority

US 92044497 A 19970829

Abstract (en)

[origin: EP0905836A2] A ridge waveguide semiconductor laser structure (100) fabricated by etching and wet oxidation. The upper cladding layer (112) is partially etched forming a ridge and a native oxide layer is wet oxidized from the remaining upper cladding layer (112) and the active region (106,108,110) outside the ridge. The deep native oxide layer (206) provides strong optical confinement to the ridge waveguide (208). Alternately, the active region (106,108,110) can be narrower than the ridge waveguide (208) in the laser structure. The ridge waveguide semiconductor laser structures with native oxide layers (206) can also be curved geometry lasers such as ring lasers (400).

IPC 1-7

H01S 3/19; **H01S 3/083**

IPC 8 full level

H01S 5/00 (2006.01); **H01S 5/227** (2006.01); **H01S 5/10** (2006.01); **H01S 5/22** (2006.01)

CPC (source: EP US)

H01S 5/227 (2013.01 - EP US); **H01S 5/10** (2013.01 - EP US); **H01S 5/1071** (2013.01 - EP US); **H01S 5/2215** (2013.01 - EP US); **H01S 5/2275** (2013.01 - EP US)

Citation (search report)

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